SiC (first generation)

Develop low-loss, compact SiC modules

SiC modules

- High-speed switching low-loss full SiC modules using SiC-SBD and MOS devices
- New-type high-temperature (200°C) compatible packages with 75% less volume than previously developed products

SiC power devices

MOSFET  SBD

* Through joint development with National Institute of Advanced Industrial Science and Technology (incorporated administrative agency)

Device structure

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